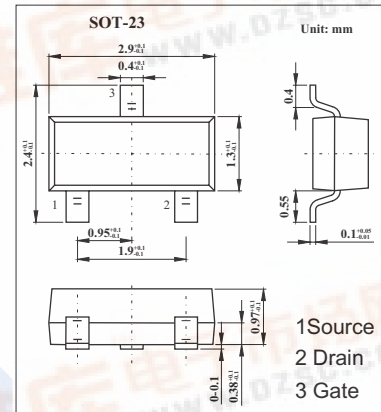


SMD Type Junction FET

N-Channel Junction Silicon FET 2SK303

■ Features

- Ideal for potentiometers, analog switches, low frequency amplifiers, constant current supplies, and impedance conversion.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to Drain voltage	V _{GDS}	-30	V
Gate current	I _G	10	m A
Drain current	I _D	20	m A
Power dissipation	P _D	200	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μ s, Duty Cycle ≤ 1%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Gate to drain	V _{GDS}	I _G = -10 μ A	-30			V
Gate to source leakage current	I _{GSS}	V _{GS} = -20V			-1.0	nA
Drain cut-off current	I _{DSS}	V _{DS} = 10V, V _{GS} = 0	0.6		12.0	mA
Cutoff voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1 μ A		-1	-4	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz	2.5	6.0		ms
Drain to source on-state resistance	R _{DS(on)}	V _{GS} = 0, V _{DS} = 10mV		250		Ω
Input capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz		5		pF
Reverse transfer capacitance	C _{rss}			1.5		pF

■ I_{DSS} Classification unit: mA

Marking	V2	V3	V4	V5
Rank	2	3	4	5
I _{DSS}	0.6~1.5	1.2~3.0	2.5~6.0	5.0~12.0